10/593878

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

Katsunori ASANO et al. Atty. Ref.: 925-354

Serial No. To be assigned TC/A.U.: To be assigned

Filed: September 22, 2006 Examiner: To be assigned

For: VOLTAGE-CONTROLLED SEMICONDUCTOR DEVICE

September 22, 2006

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

INFORMATION DISCLOSURE STATEMENT

As suggested by 37 C.F.R. 1.97, the undersigned attorney brings to the attention of the Patent and Trademark Office the references listed on the attached form PTO/SB/08a. Copies of the International Search Report and cited references are attached.

This is not to be construed as a representation that a search has been made or that no better prior art exists, or that a reference is relevant merely because cited.

The Examiner is requested to initial the attached form PTO/SB/08a and to return a copy of the initialed document to the undersigned as an indication that the attached references have been considered and made of record.

Respectfully submitted,

NIXON & VANDERHYE P.C.

By:

H. Warren Burnam, Jr Reg. No. 29,366

HWB:klm 901 North Glebe Road, 11th Floor Arlington, VA 22203-1808 Telephone: (703) 816-4000

Facsimile: (703) 816-4100

IADIC BEN'A DATIDIO OO CED 2000 PTO/SB/08a

heet 1 of 1	141 10 1166 0 FC1/FIO 22 2EP 2006		
INFORMATION DISCLOSURE CITATION	ATTY. DOCKET NO.	SERIAL NO. / F 07 9 7 9	
	925-354	To be assigned 3878	
	APPLICANT		
	Katsunori ASANO et al.		
(Use several sheets if necessary)	FILING DATE	TC/A.U.	
	September 22, 2006	To be assigned	
	LLO DATENT DOCUMENTO		
CVANINED	U.S. PATENT DOCUMENTS	FILINO S	

			J.S. PATENT DOCUMENTS			
*EXAMINER					4.00	FILING DATE
INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	IF APPROPRIATE
	5,917,204	6/1999	Bhatnagar et al.			
					 	
					,	
			1			
1						
	+					
				1		
						
		ΕΛΙ	REIGN PATENT DOCUMENTS		•	
		FUI	TEIGHT FATENT DOCUMENTS			TRANCI ATION

TRANSLATION **DOCUMENT** DATE COUNTRY SUBCLASS CLASS **YES** 2003-31802 1/2003 Japan ABSTRACT 2001-291869 10/2001 Japan ABSTRACT 2002-231947 08/2002 ABSTRACT Japan 10/1998 10-284733 Japan ABSTRACT 10-256529 09/1998 Japan ABSTRACT 10-27899 01/1998 Japan ABSTRACT

OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.) International Search Report of PCT/JP2005/004834 mailed 28 June 2005 Ryu et al., "High-Power P-Channel UMOS IGBT'S in 6H-SiC for High Temperature Operation", Materials Science Forum, Vols. 338-342, pp. 1427-1430 (2000) *Examiner Date Considered

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.